

List of Publications

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Books:

Tong, Q.-Y., and U. Gösele. Semiconductor wafer bonding: science and technology. Electrochemical Society. Graduate Series, Wiley, New York (1999).

Alexe, M., and U. Gösele, eds., Wafer Bonding: Applications and Technology. Springer, Berlin (2004)

Book Chapters and Review Articles

Frank, W., U. Gösele, H. Mehrer, and A. Seeger. Diffusion in silicon and germanium. In: *Diffusion in Crystalline Solids*, Eds. G. Murch and A. S. Nowick, 63. Academic Press, New York (1984).

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Mitani, K., and U. Gösele. Wafer bonding technology for silicon-on-insulator applications: A review. In: *Journal of Electronic Materials* **21**, 669-676 (1992).

Gösele, U. Diffusion and diffusion-induced defects in silicon. In: *Encyclopedia of Advanced Materials*, Ed. S. Mahajan, 629-636. Pergamon Press (1993).

Gösele, U., and V. Lehmann. Porous silicon quantum spong structures: formation mechanism, preparation methods and some properties. In: *Porous Silicon*, Eds. Z. Ch. Feng and R. Tsu, 17-39. World Scientific, London (1994).

Tong, Q.-Y., and U. Gösele. Silicon wafer bonding - recent developments. In: *Materials Chemistry and Physics*, **37**, 101-127 (1994).

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